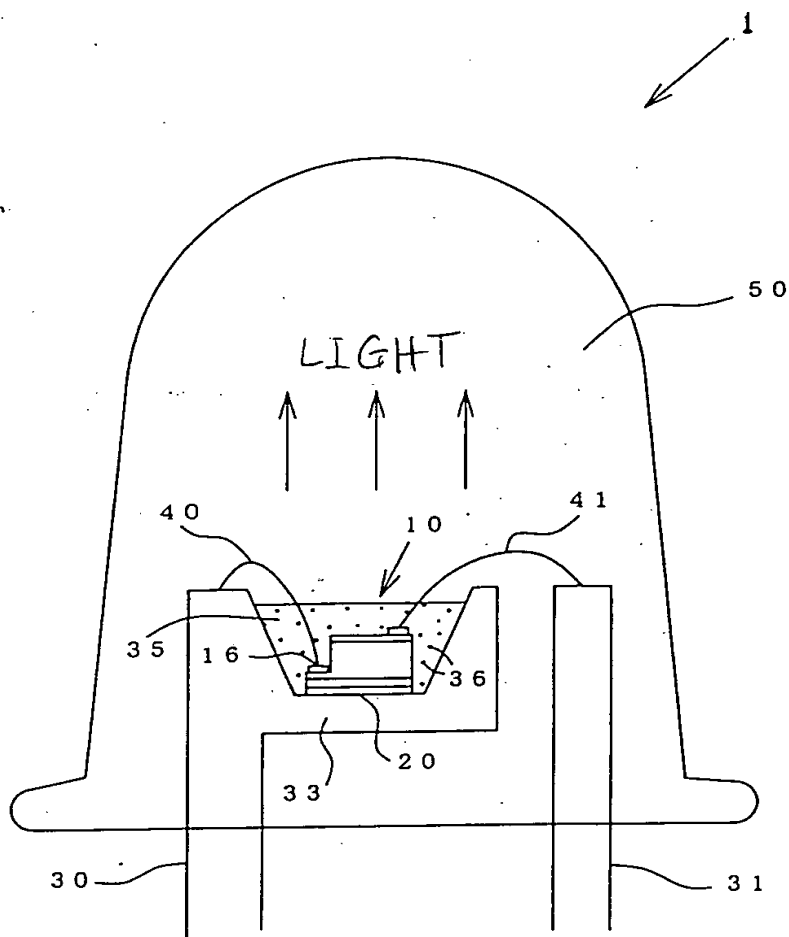
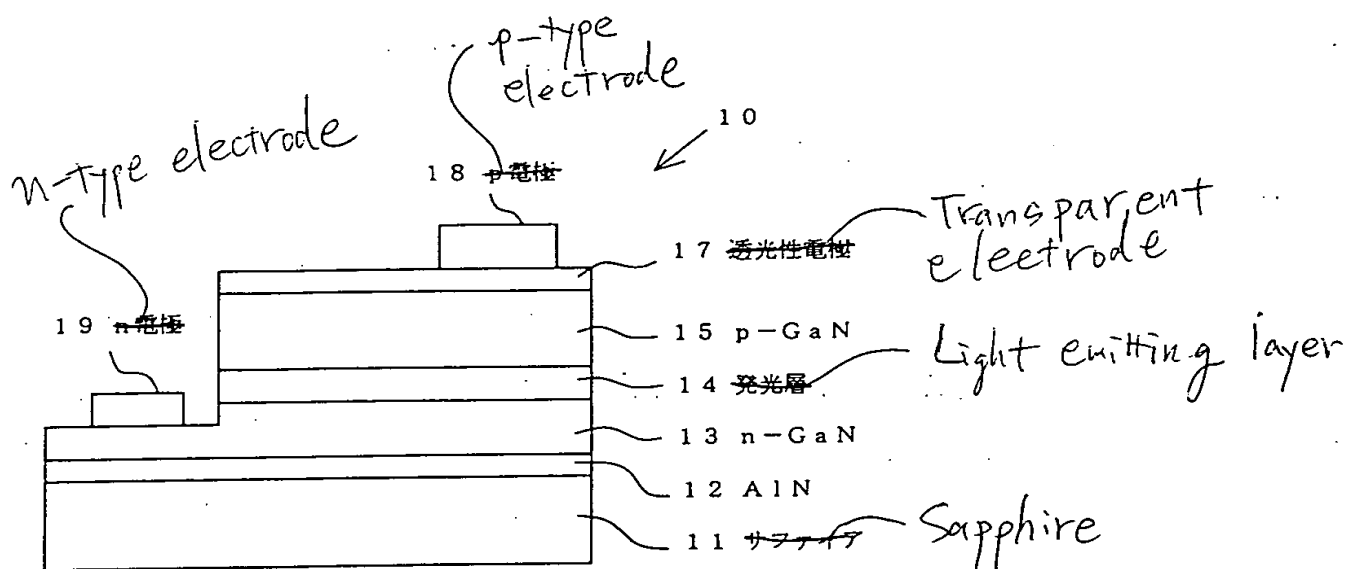


FIG. 1



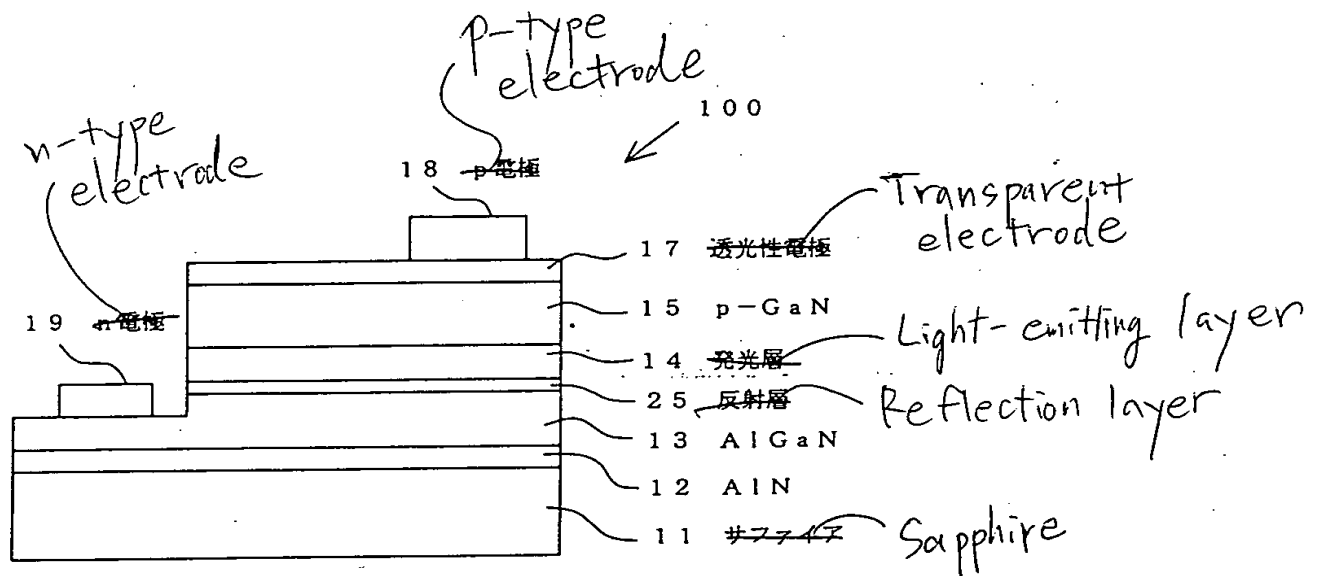
09654501.090100

FIG. 2



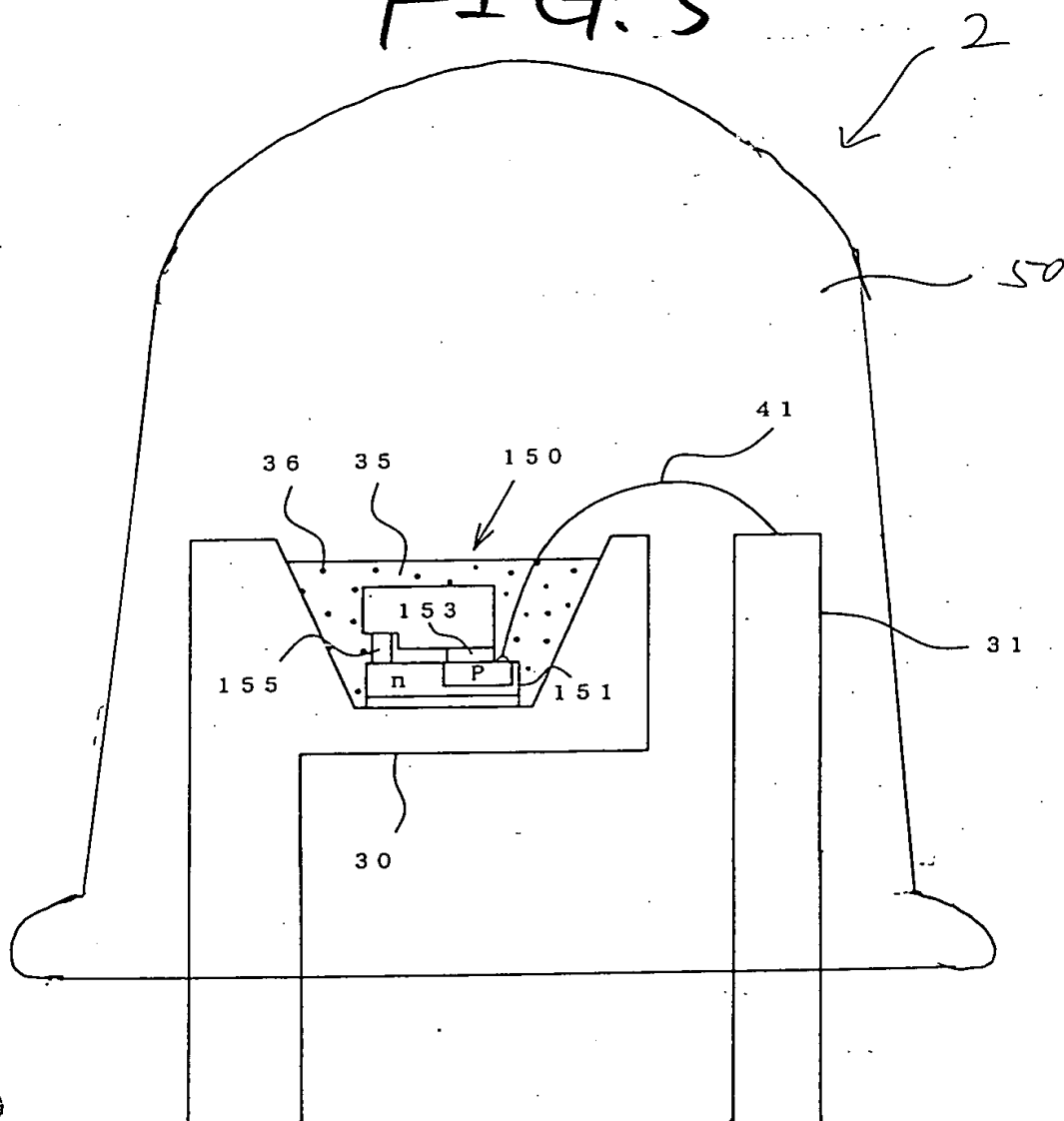
001060-1054501-090100

FIG. 3



A cross-sectional diagram of a GaN-based LED structure. The diagram shows a stack of layers on a substrate. From bottom to top, the layers are: a reflection layer (26), a sapphire layer (11), an AlN layer (12), an n-GaN layer (13), a light emitting layer (14), a p-GaN layer (15), and a transparent electrode (17). On top of the transparent electrode, there is a p-type electrode (18) and an n-type electrode (19). Handwritten labels in Japanese and English identify these components: 'p-type electrode' (18), 'n-type electrode' (19), '透明性電極' (transparent electrode, 17), 'p-GaN' (15), '発光層' (light emitting layer, 14), 'n-GaN' (13), 'AlN' (12), 'サファイア' (sapphire, 11), and '反射層' (reflection layer, 26). The number '101' is also present near the top right.

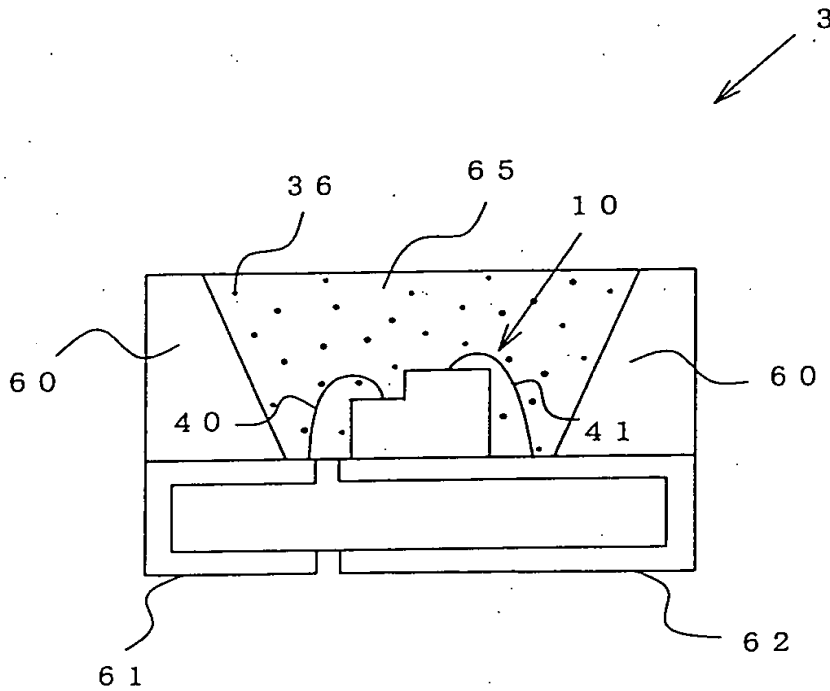
FIG. 5



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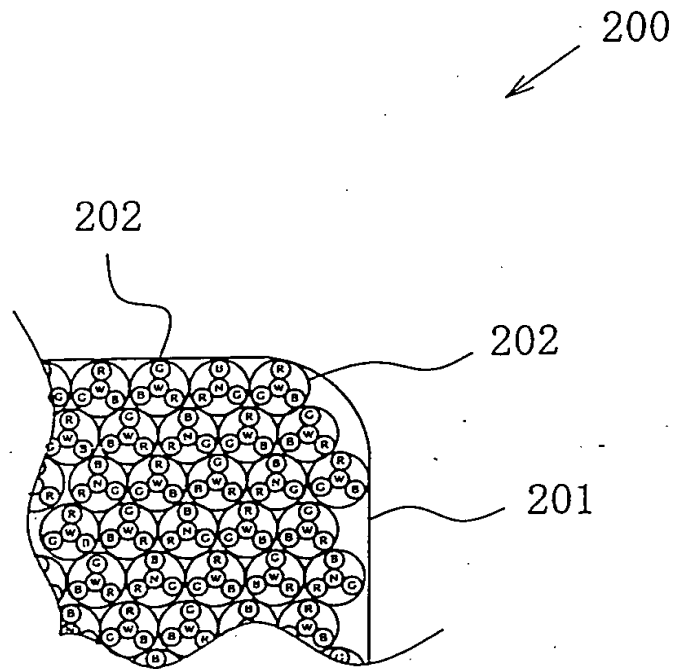


FIG. 6



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FIG 7



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FIG. 8

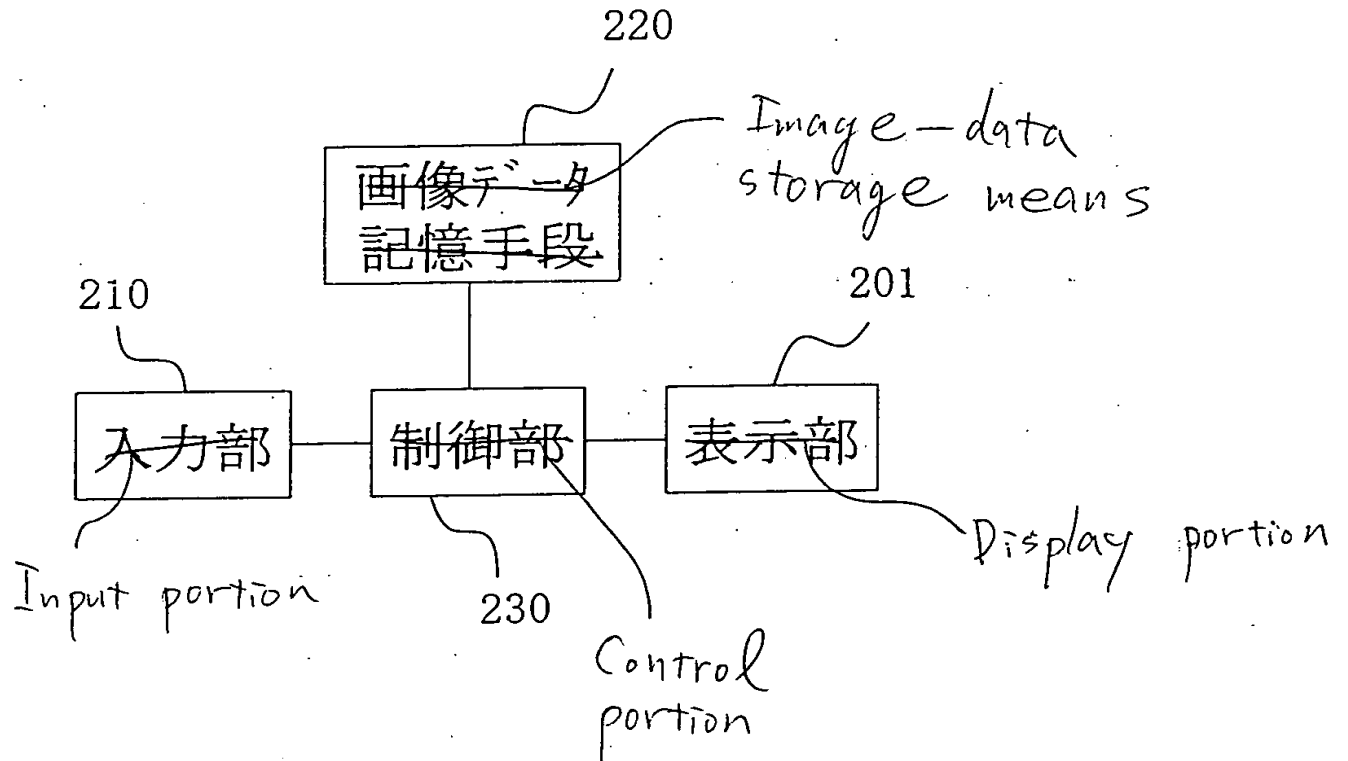
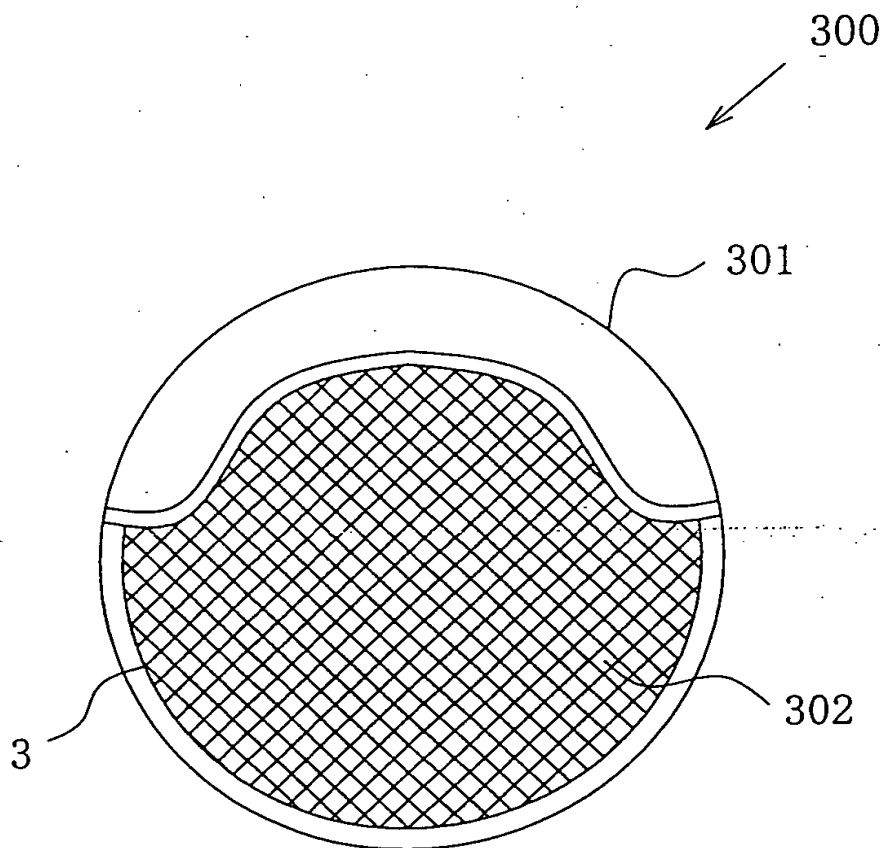




FIG. 9



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FIG. 10A

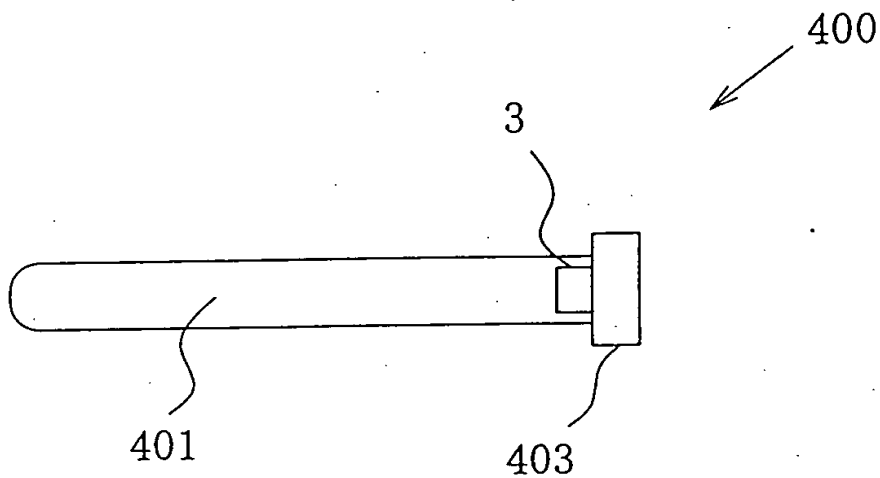


FIG. 10B

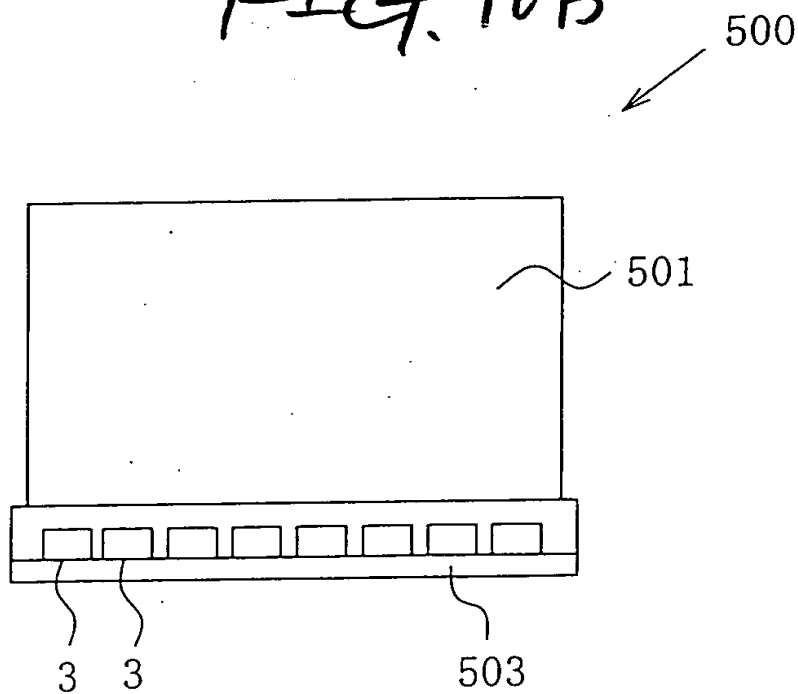
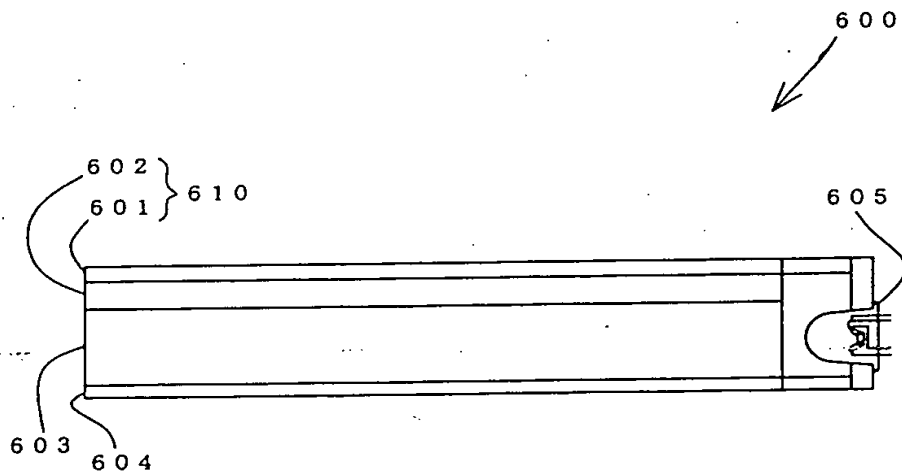
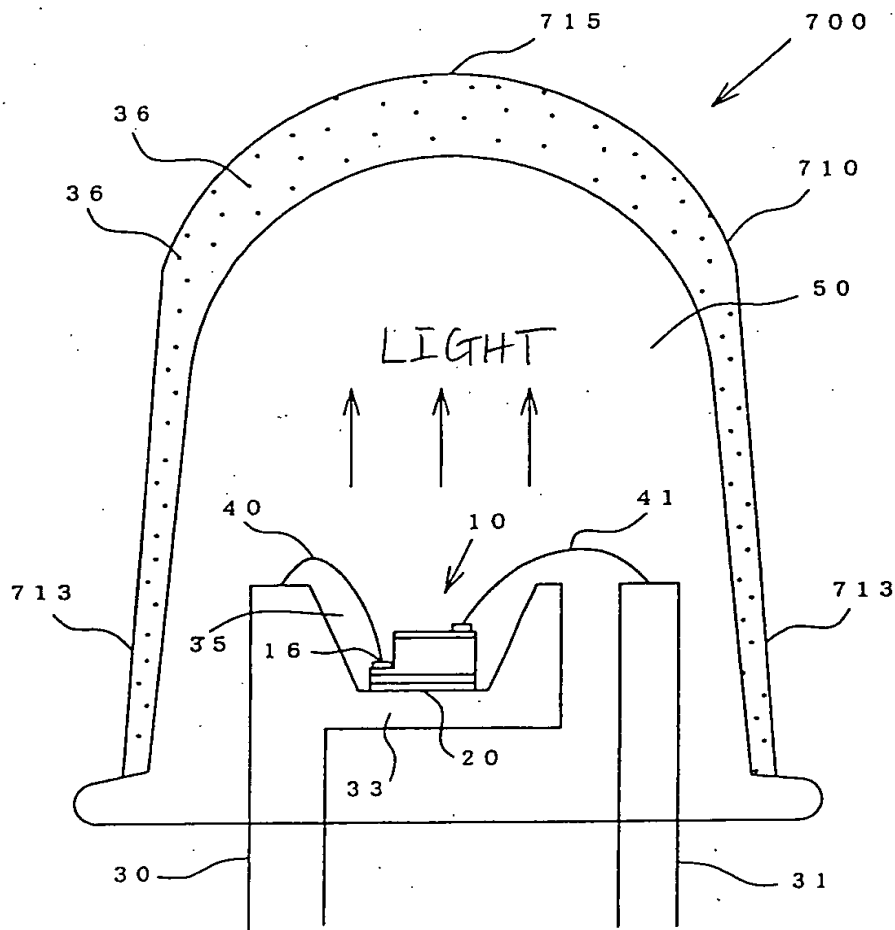


FIG. 11



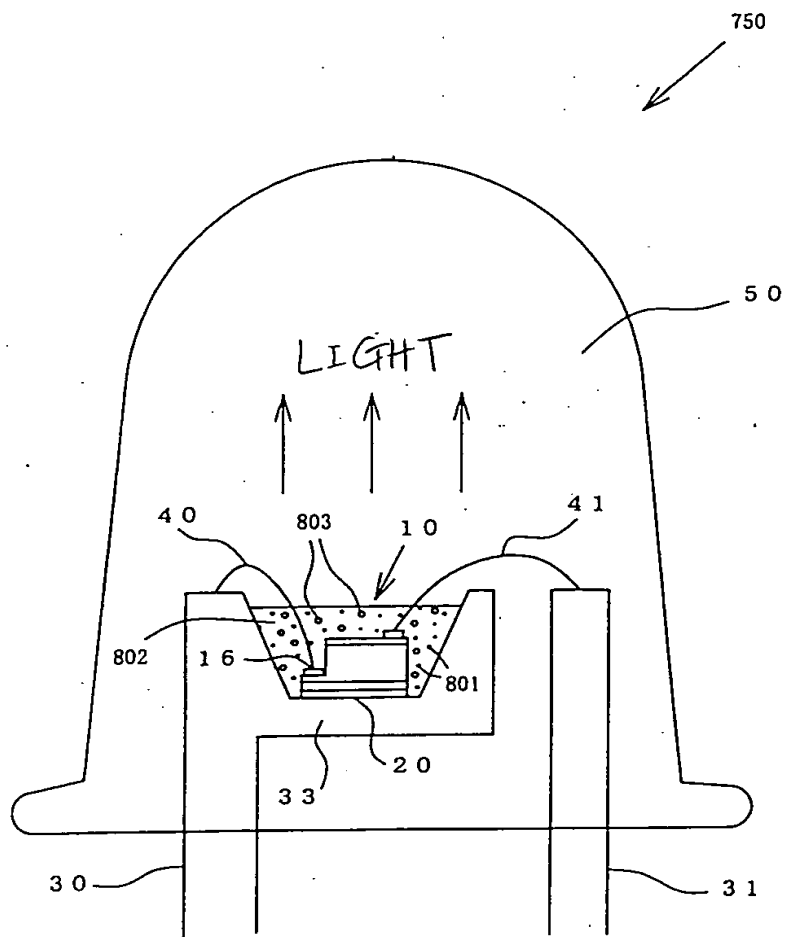
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FIG. 12



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FIG. 13



00T060" T0545960

FIG. 14

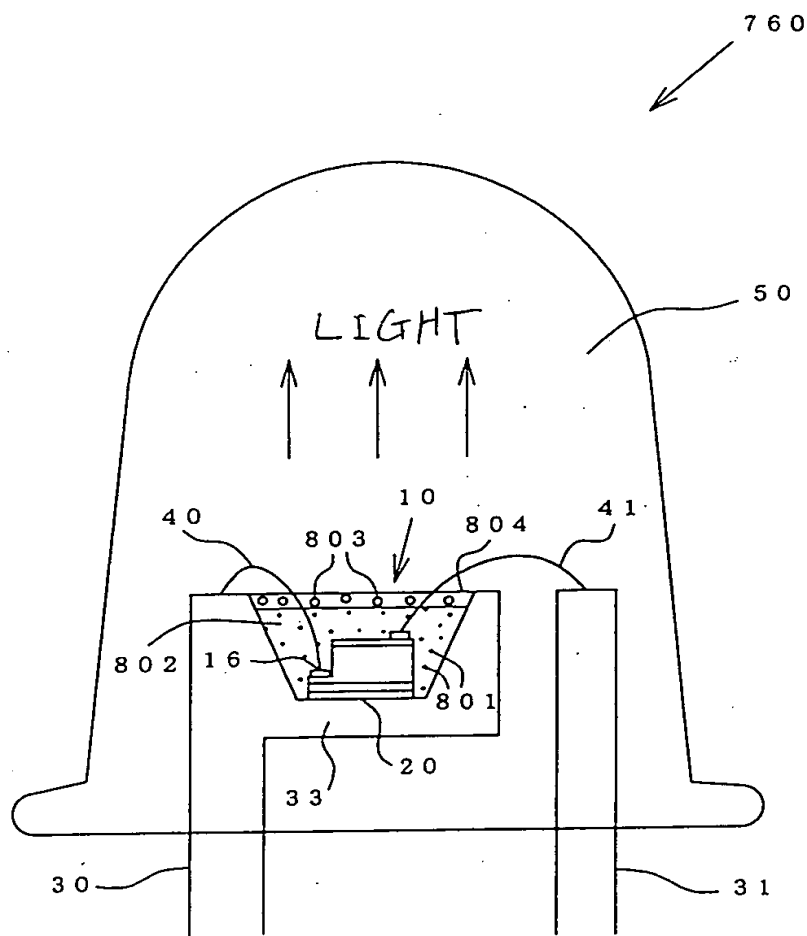
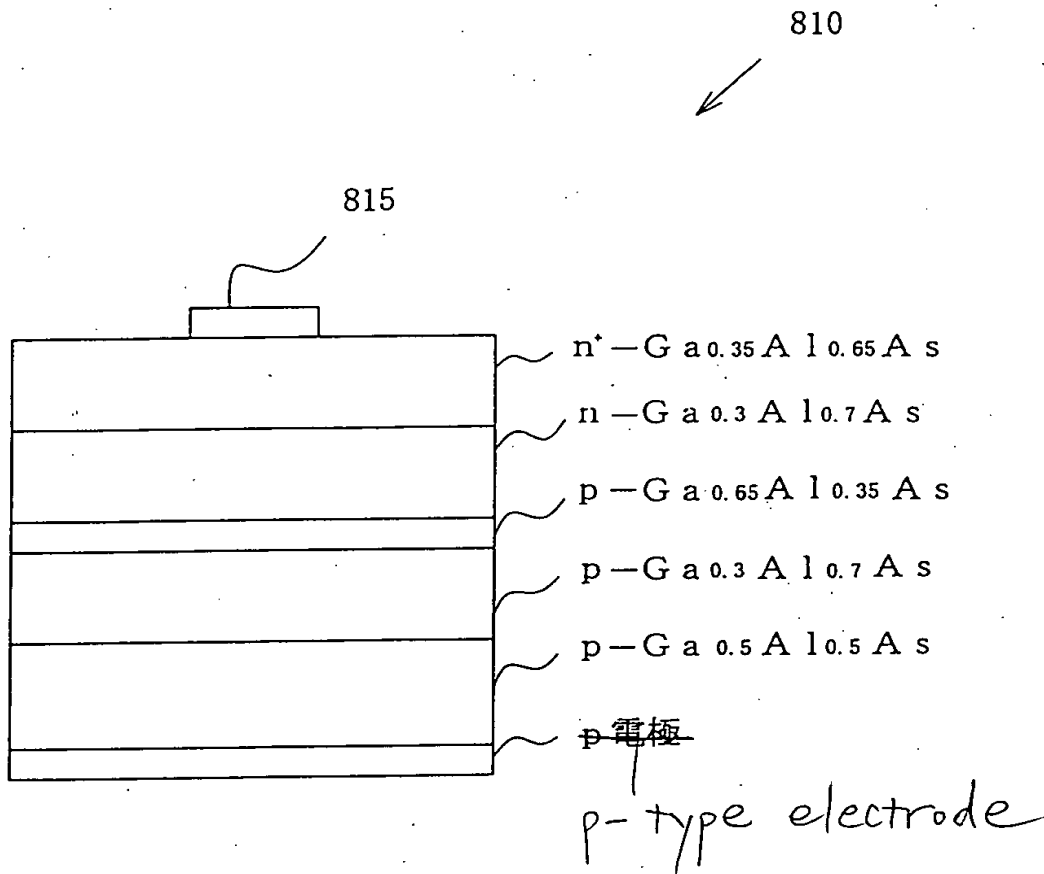




FIG. 16



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FLG. 17

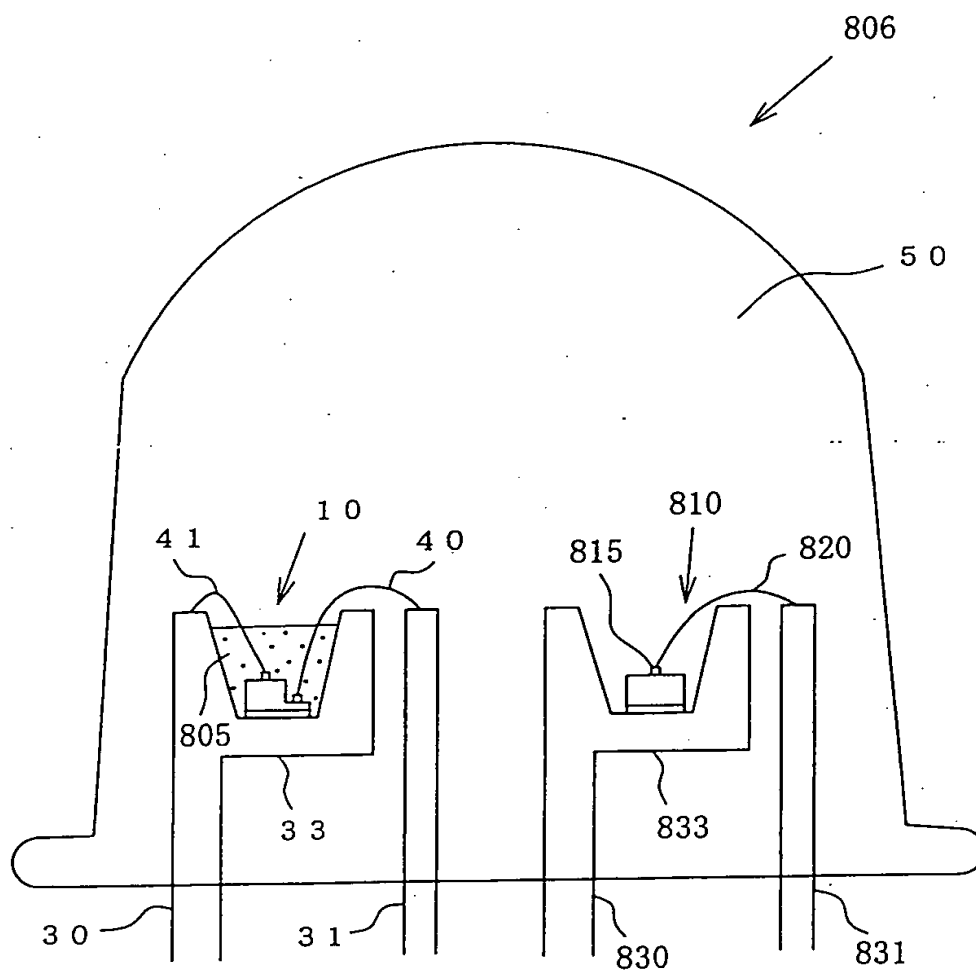


FIG. 18

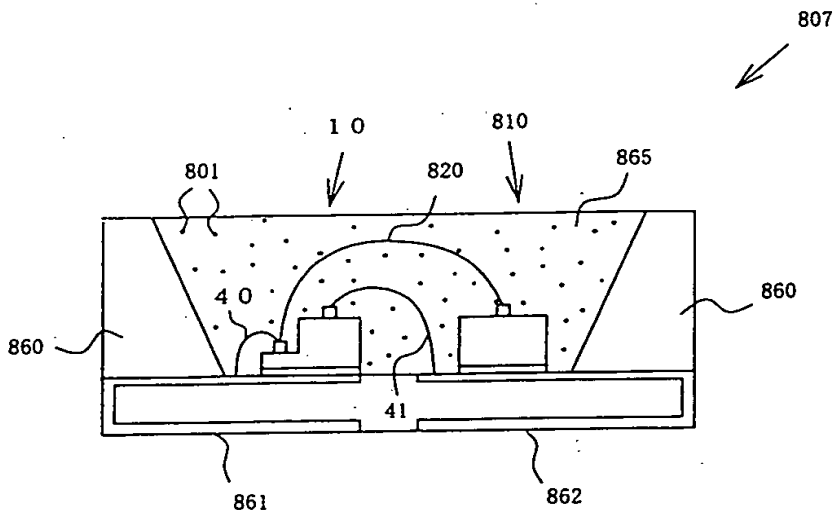
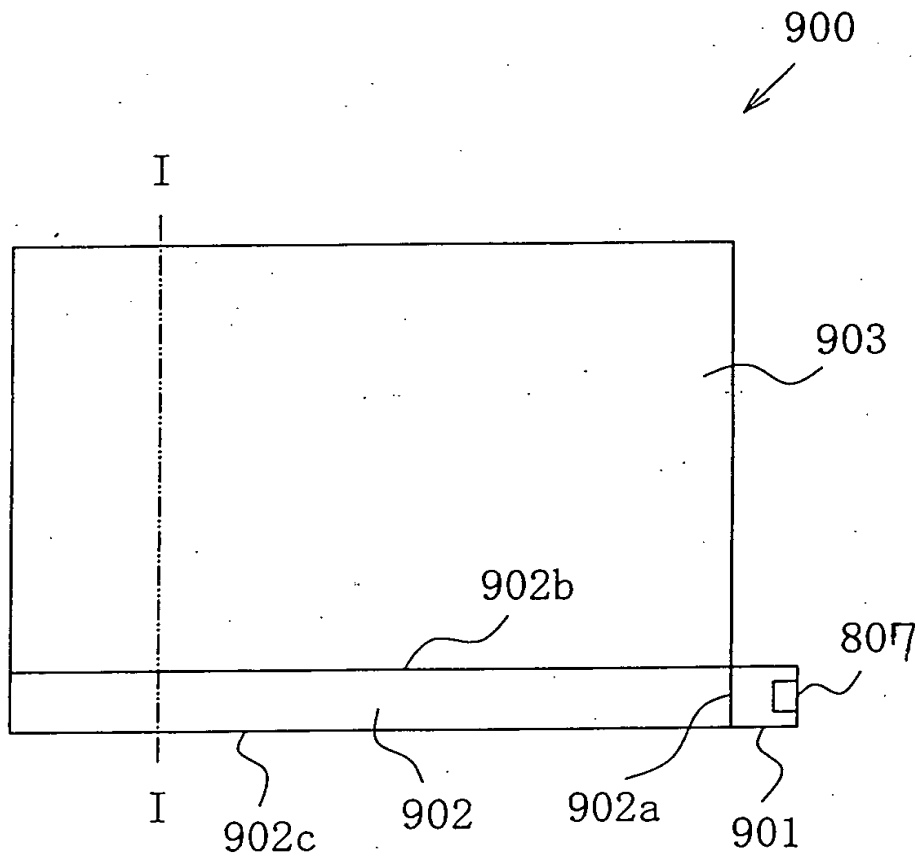
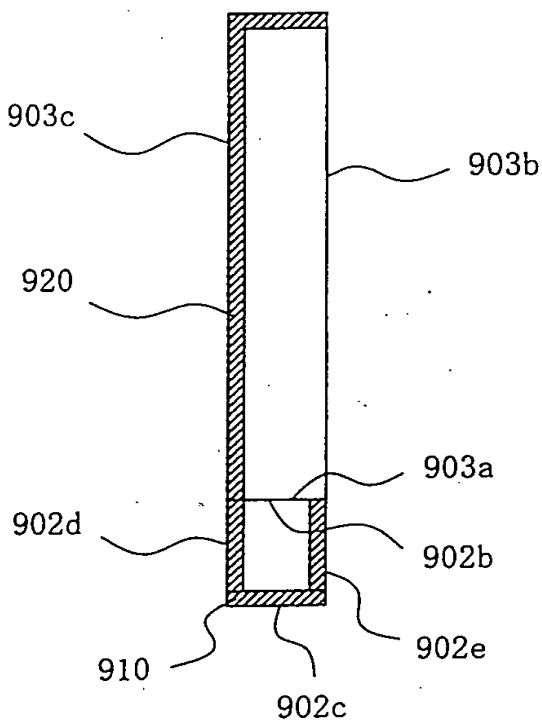


FIG. 19



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FIG. 20



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